

Status of the Barrel Strip Sensors

Choice of Technology and Qualification



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PANDA Coll. Meeting
March 10th, 2014

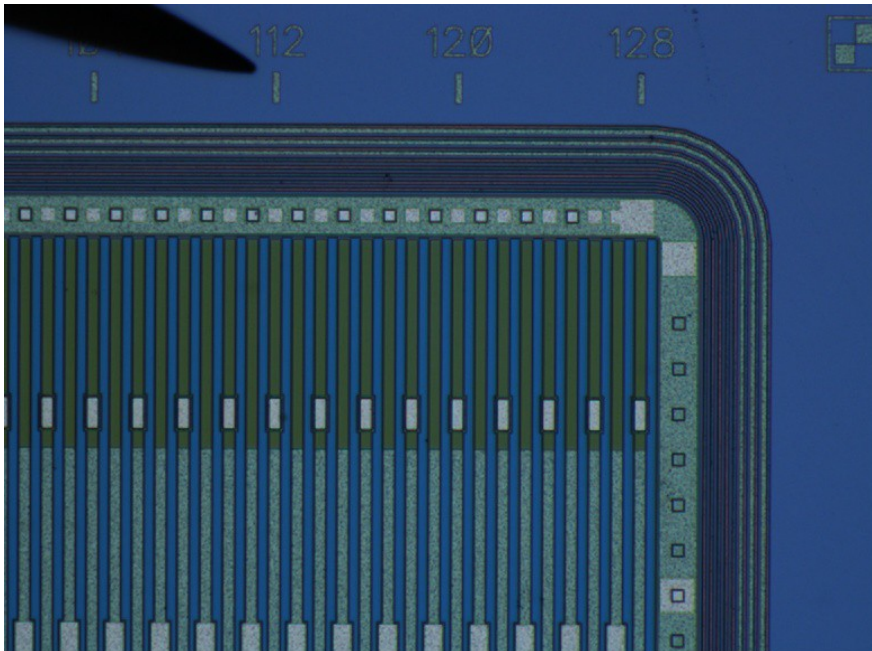


Prototype Sensors

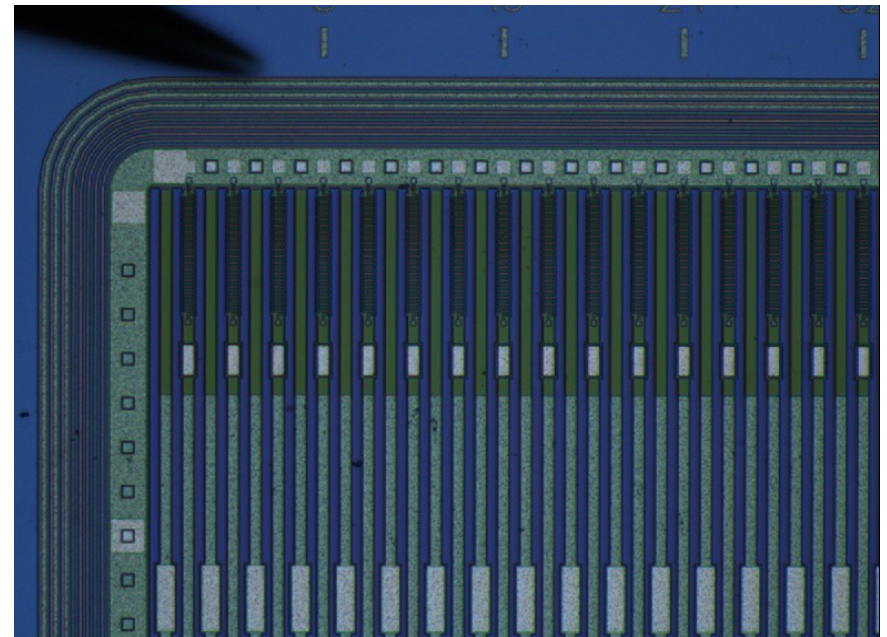
Prototyping Runs

Run	Year	Biasing	Resistivity	Vdep	Thickn.
CIS 01	2010	punch-through	5.2 k Ω cm	50	285+-10
CIS 02	2013	poly-Si	2.8 k Ω cm	100	285+-10

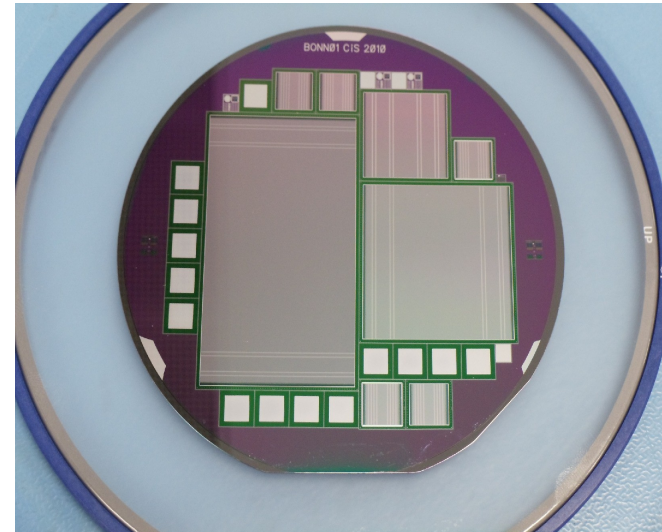
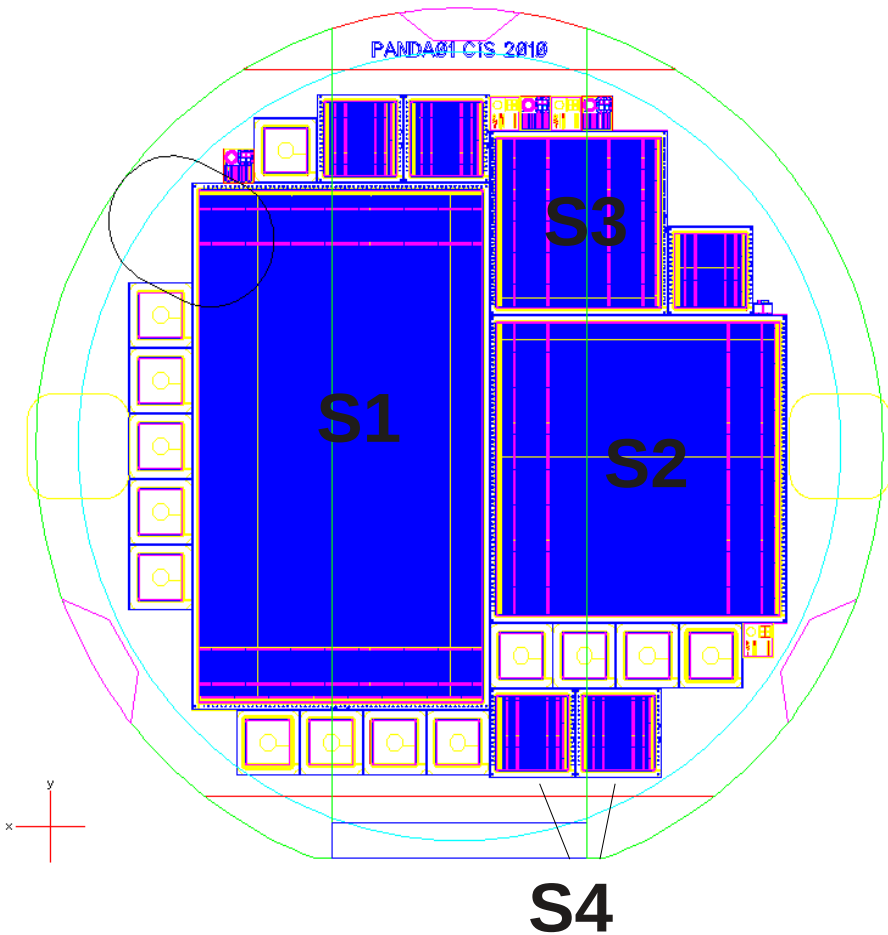
CIS01



CIS02

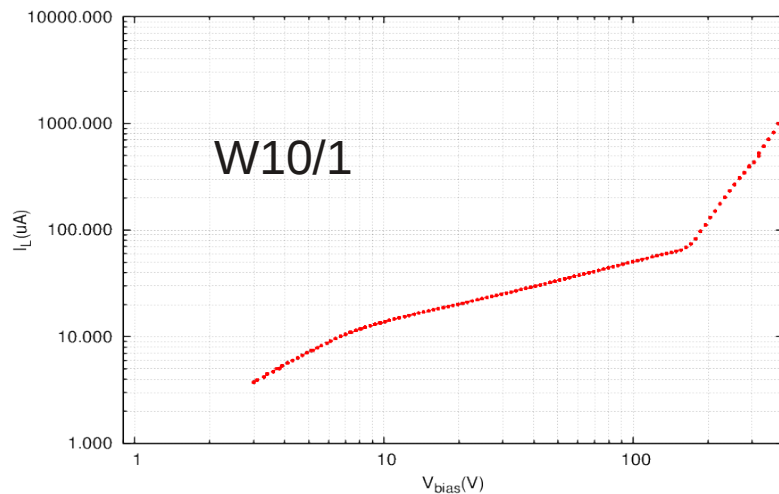
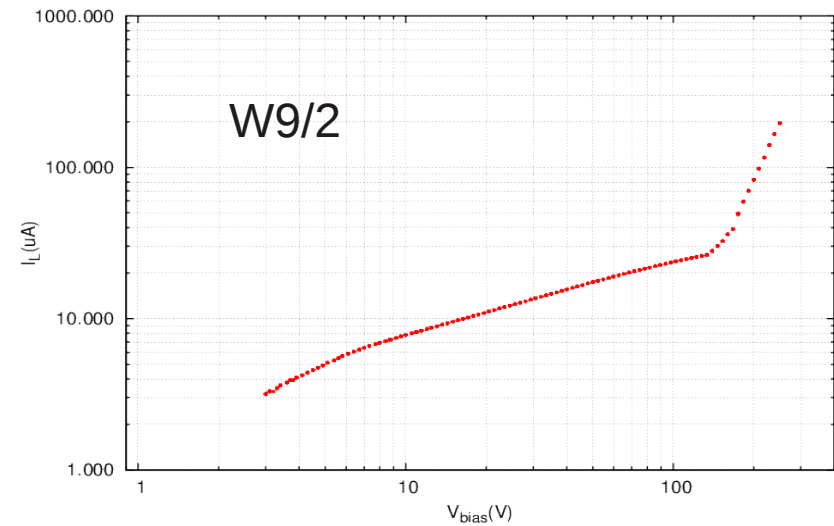
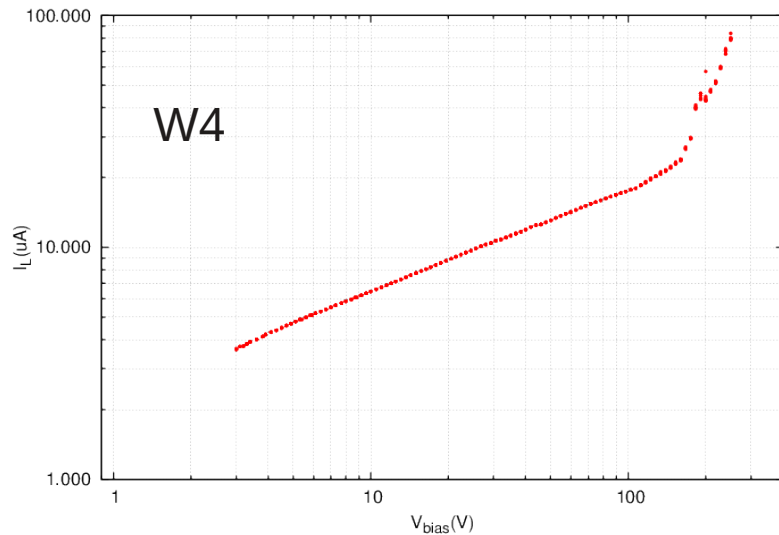


Prototype Sensors



S1			
<i>p</i> -side/ <i>n</i> -side strips	896/512		
pitch/width	65/30	μm	
active area	58.275×33.315	mm^2	
S2			
<i>p</i> -side/ <i>n</i> -side strips	512/512		
pitch/width	65/30	μm	
active area	33.315×33.315	mm^2	
S3			
<i>p</i> -side/ <i>n</i> -side strips	384/384		
pitch/width	50/20	μm	
active area	19.230×19.230	mm^2	
S4			
<i>p</i> -side/ <i>n</i> -side strips	128/128		
pitch/width	65/30	μm	
active area	8.355×8.355	mm^2	

Prototype Sensors



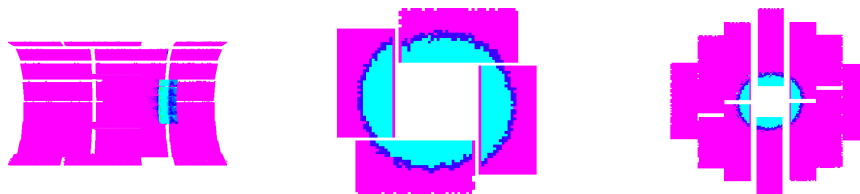
Problem with CIS 01 Sensors: Early Breakdown

- Many sensors show breakdown at $< 250\text{V}$
- Depletion behavior at higher irradiation doses not accessible $\rightarrow$ no QA
- CIS 02: Breakdown $> 460\text{V}$ $\rightarrow$ ok

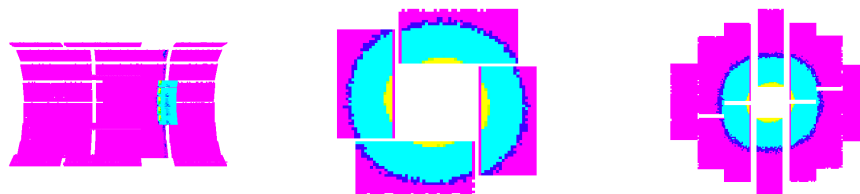
Radiation Hardness

Pixel barrels/disks

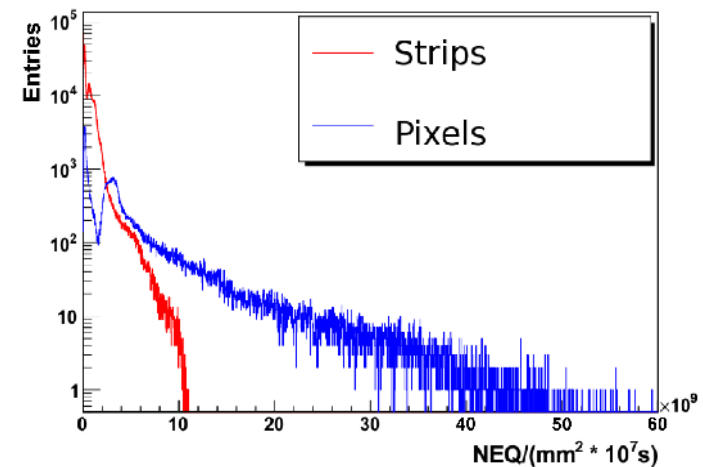
2GeV



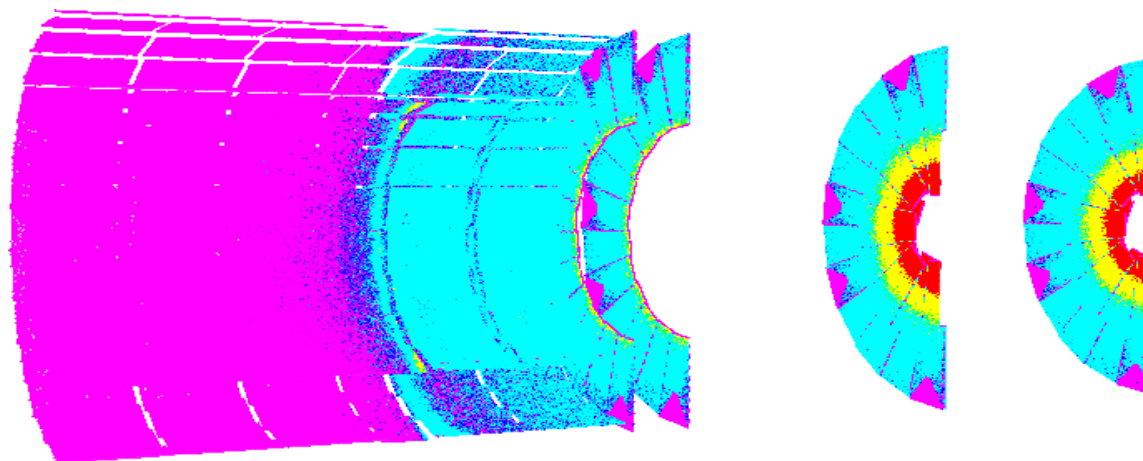
15GeV



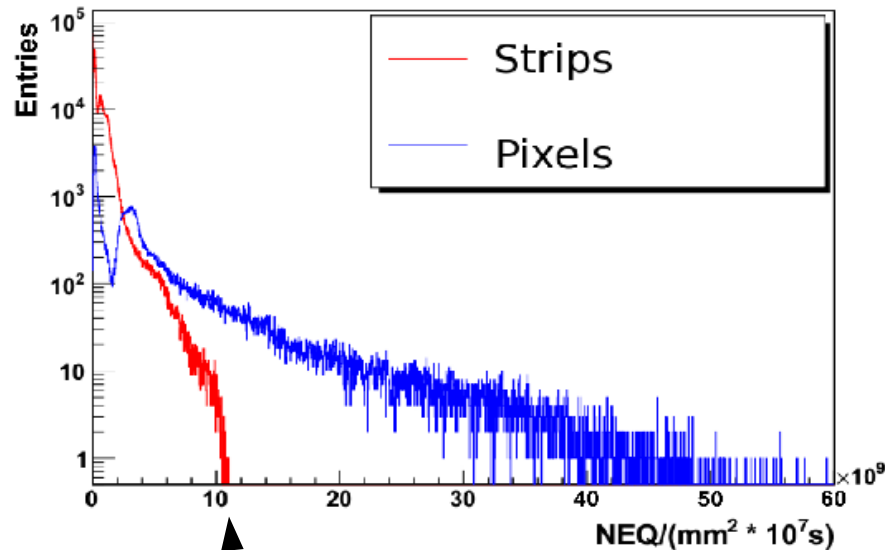
pp DPM calculations
(Tobias)



Strip barrels/disks @ 15GeV



Radiation Hardness



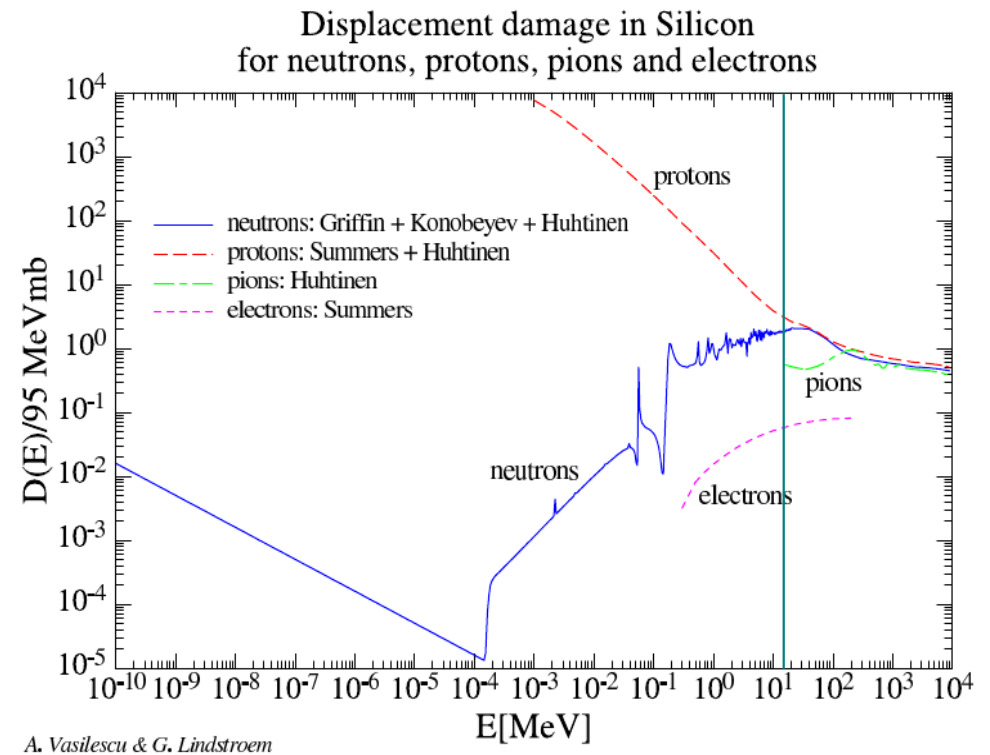
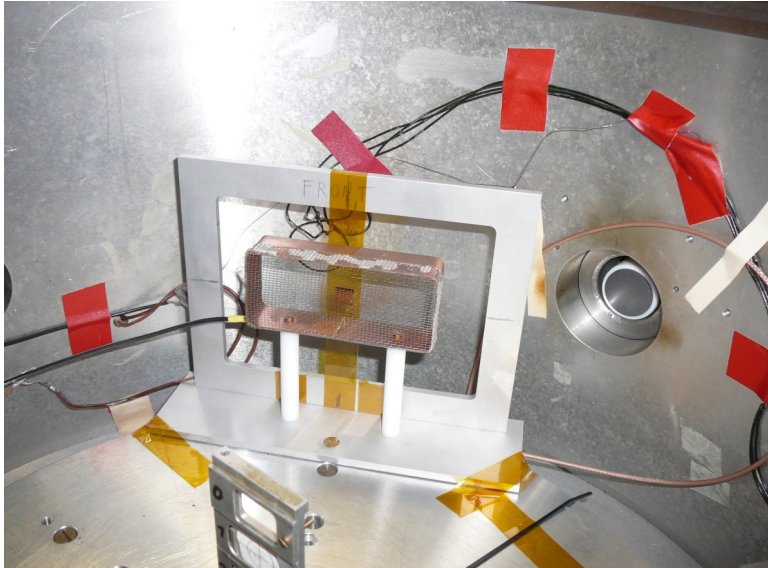
$\sim 1.1 \cdot 10^{10} \text{ neq}/(\text{mm}^2 \cdot 10^7 \text{s})$

corresponds to $\sim 3.5 \cdot 10^{13} \text{ neq}$

- for 10 years operation
- 100% duty cycle

Sensor Irradiation

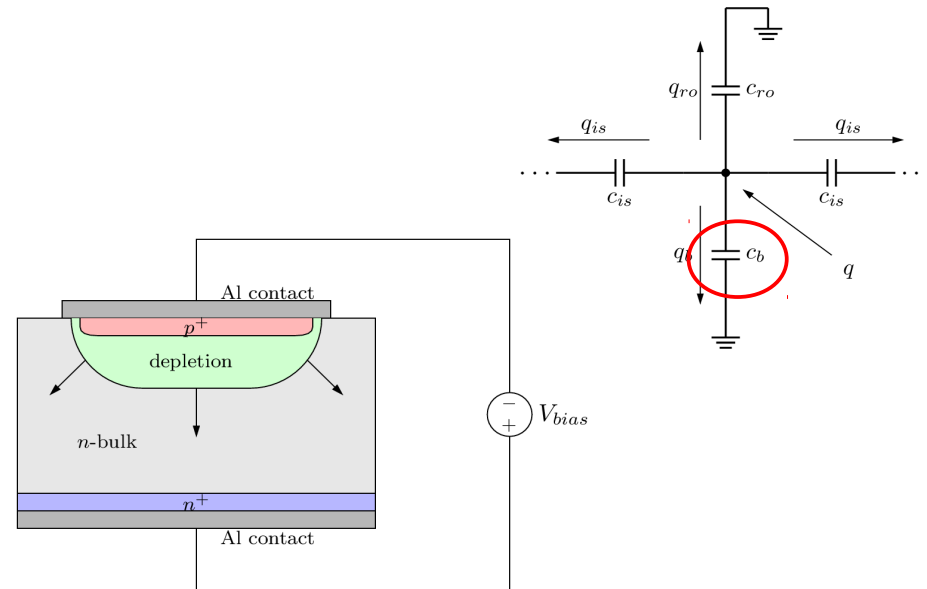
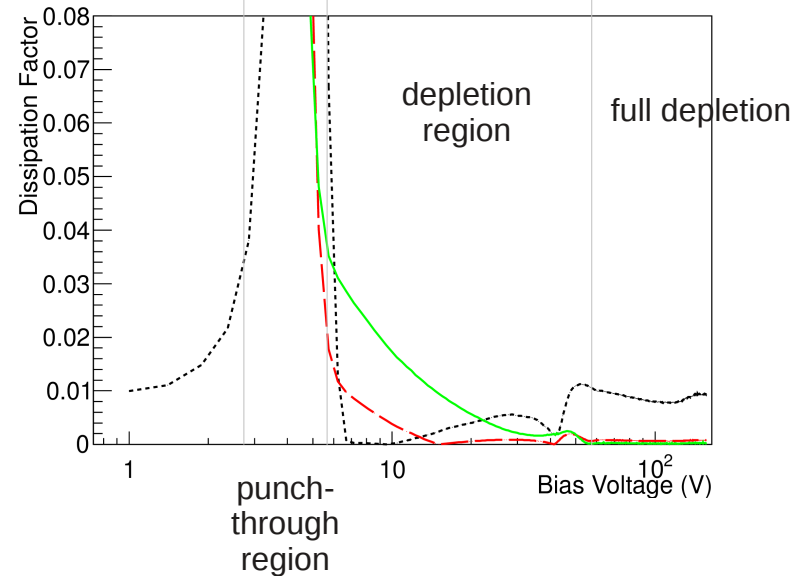
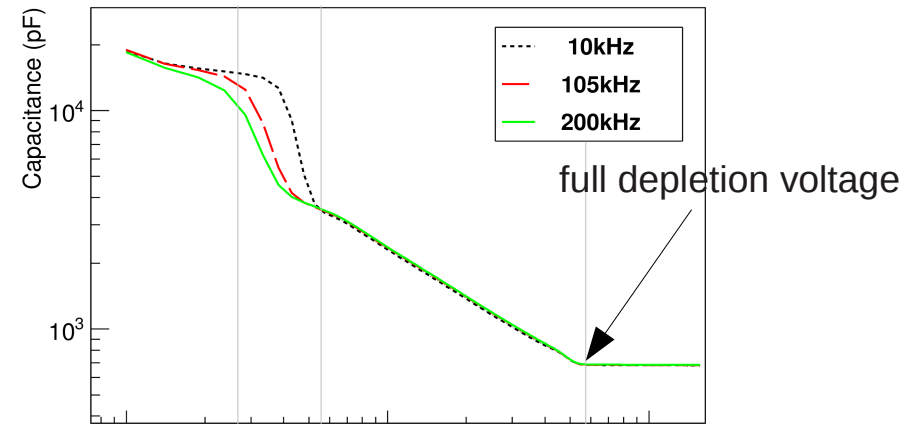
Proton irradiation at Bonn isochrone cyclotron, $T=14$ MeV



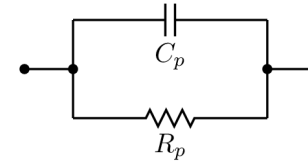
14 MeV protons: $D \approx 3$

Sensor Characterization

back side capacitance



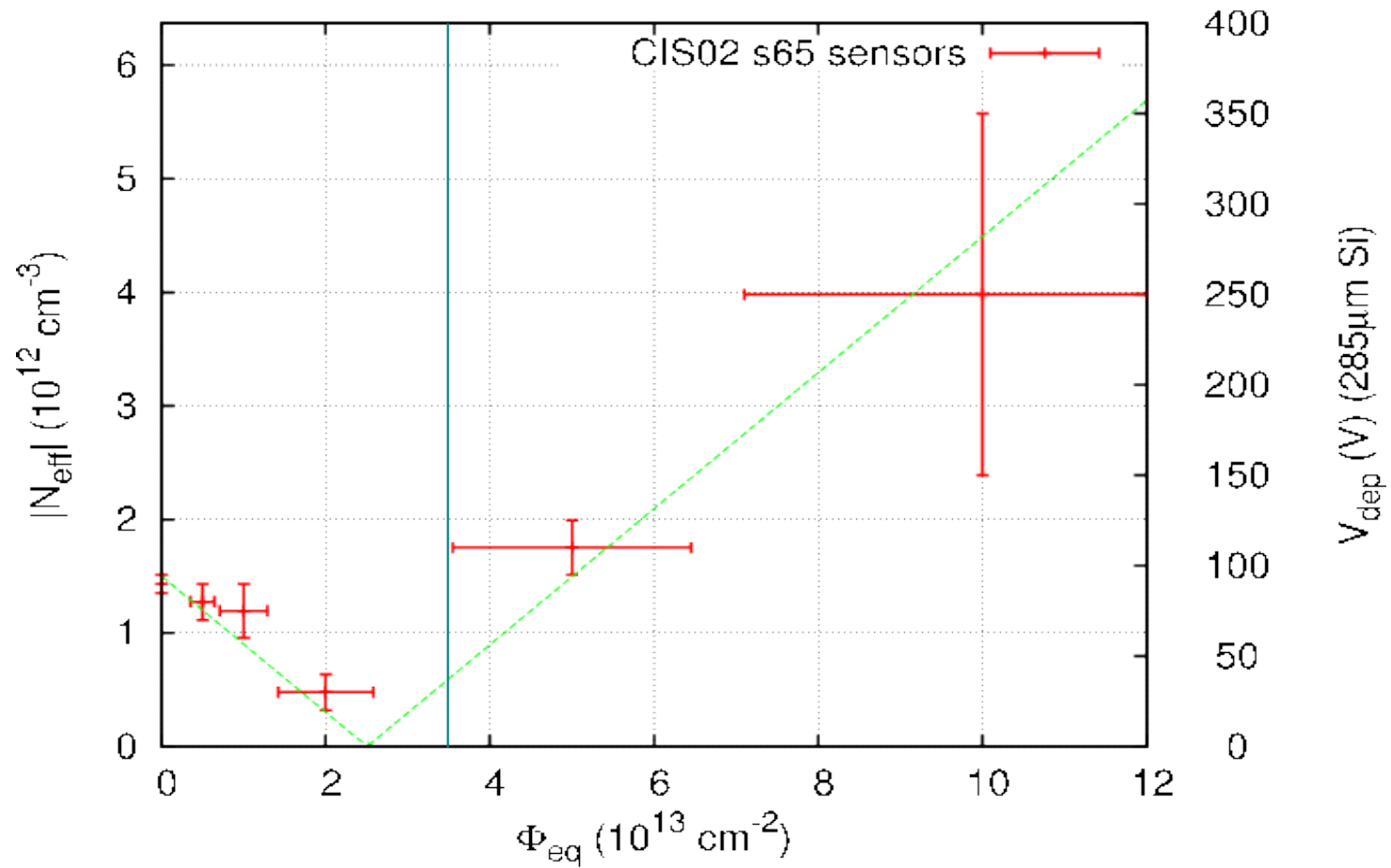
complex impedance Z



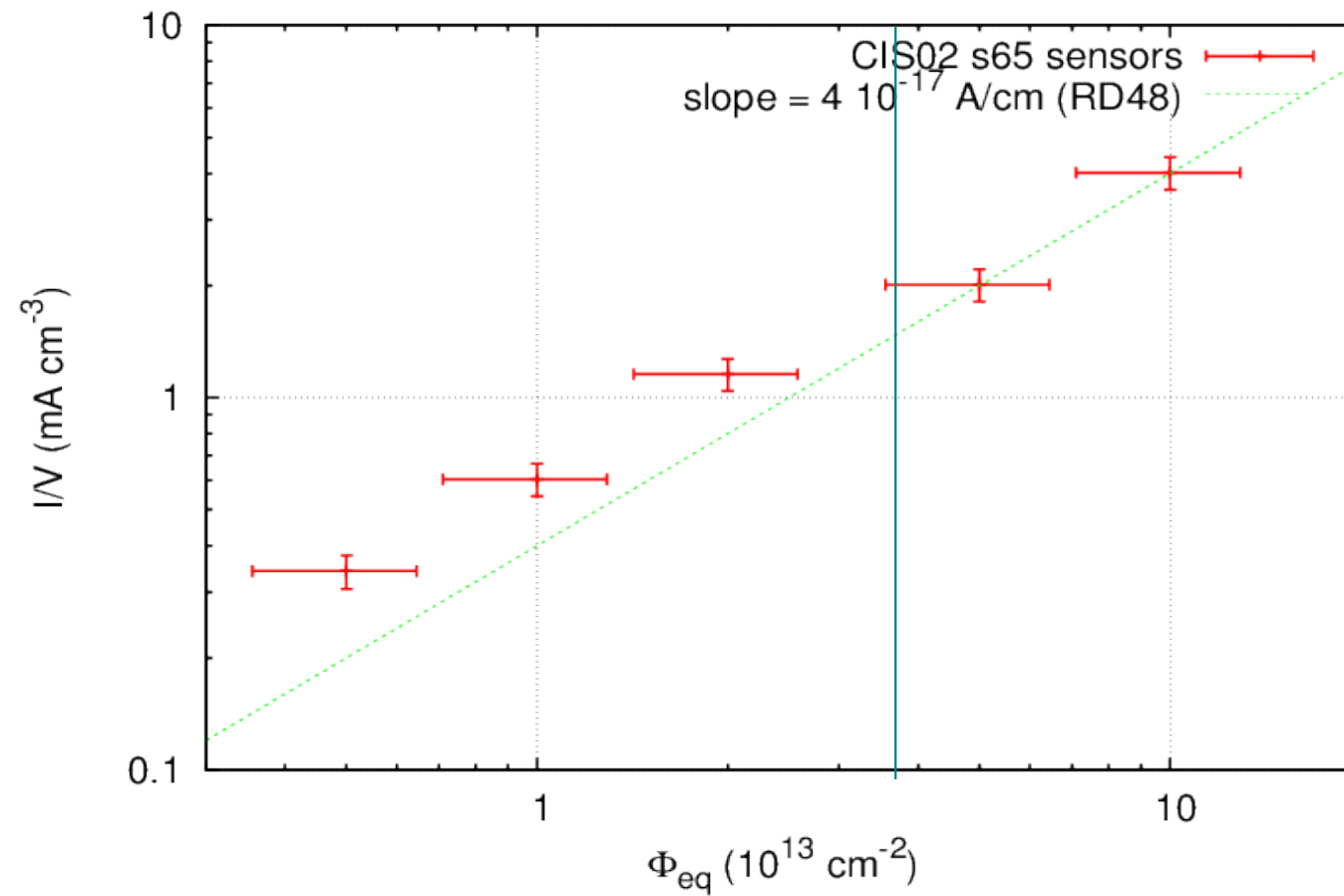
$$D = \tan \delta = \frac{\text{Re } Z}{\text{Im } Z} = \frac{1}{\omega C_p R_p}$$

Handle on depletion behavior of sensors

Radiation Hardness

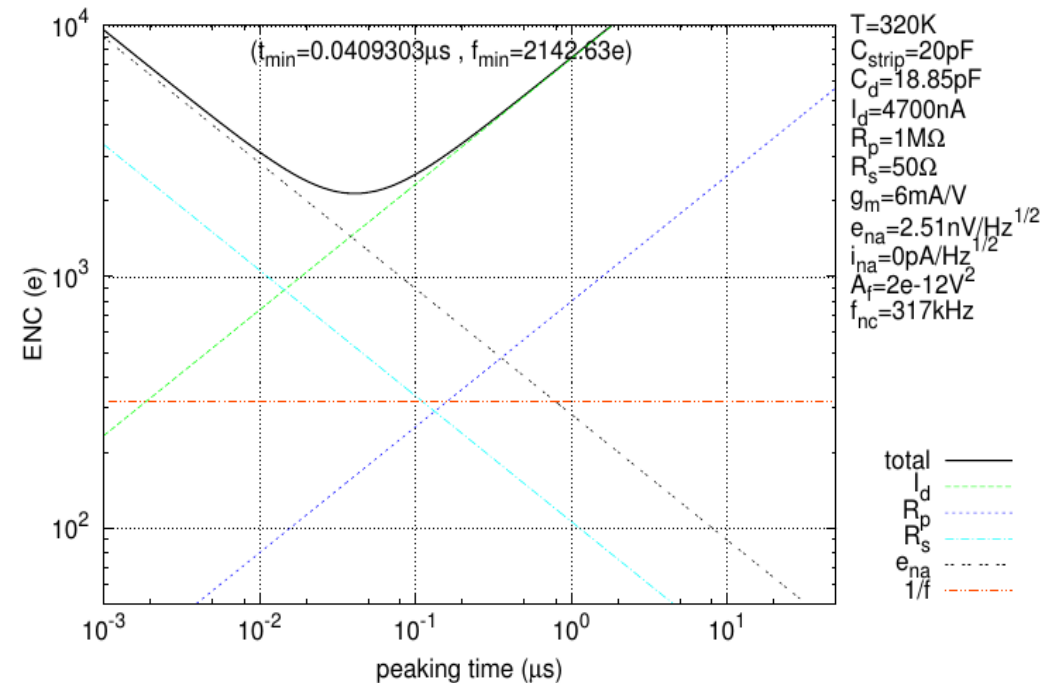
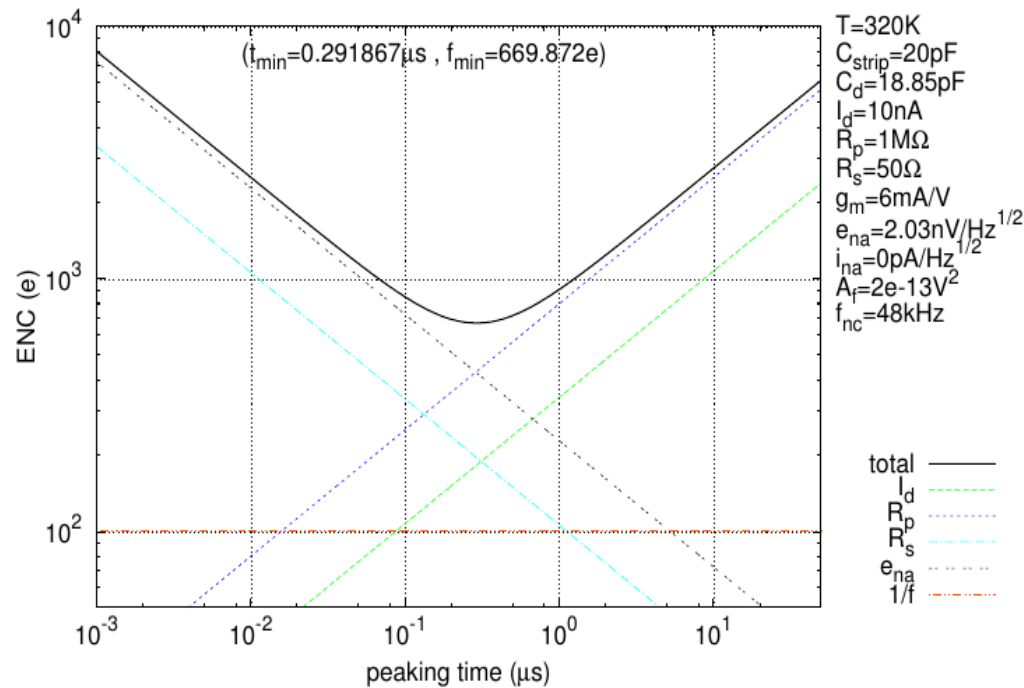


Radiation Hardness



Radiation Hardness

Total Noise: $q_n^2 = \sum_i q_{n,i}^2$



$$q_{n_{I_L}}^2 = A \cdot 2eI_L \cdot \tau$$

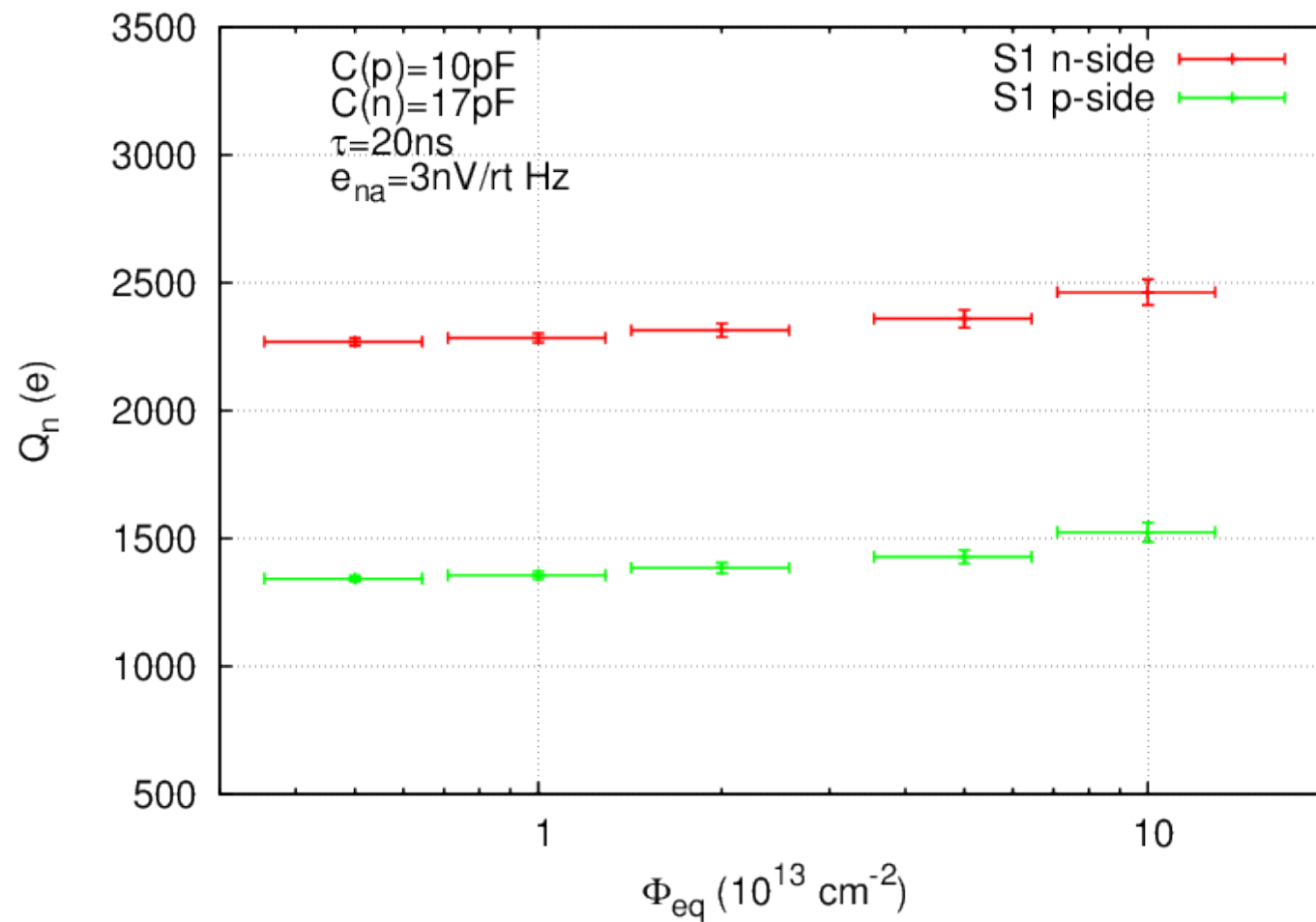
$$q_{n_A}^2 = A \cdot e_{na}^2 \cdot \frac{C_{strip}^2}{\tau}$$

$$A \approx 1 \quad (\text{Shaper Constant})$$

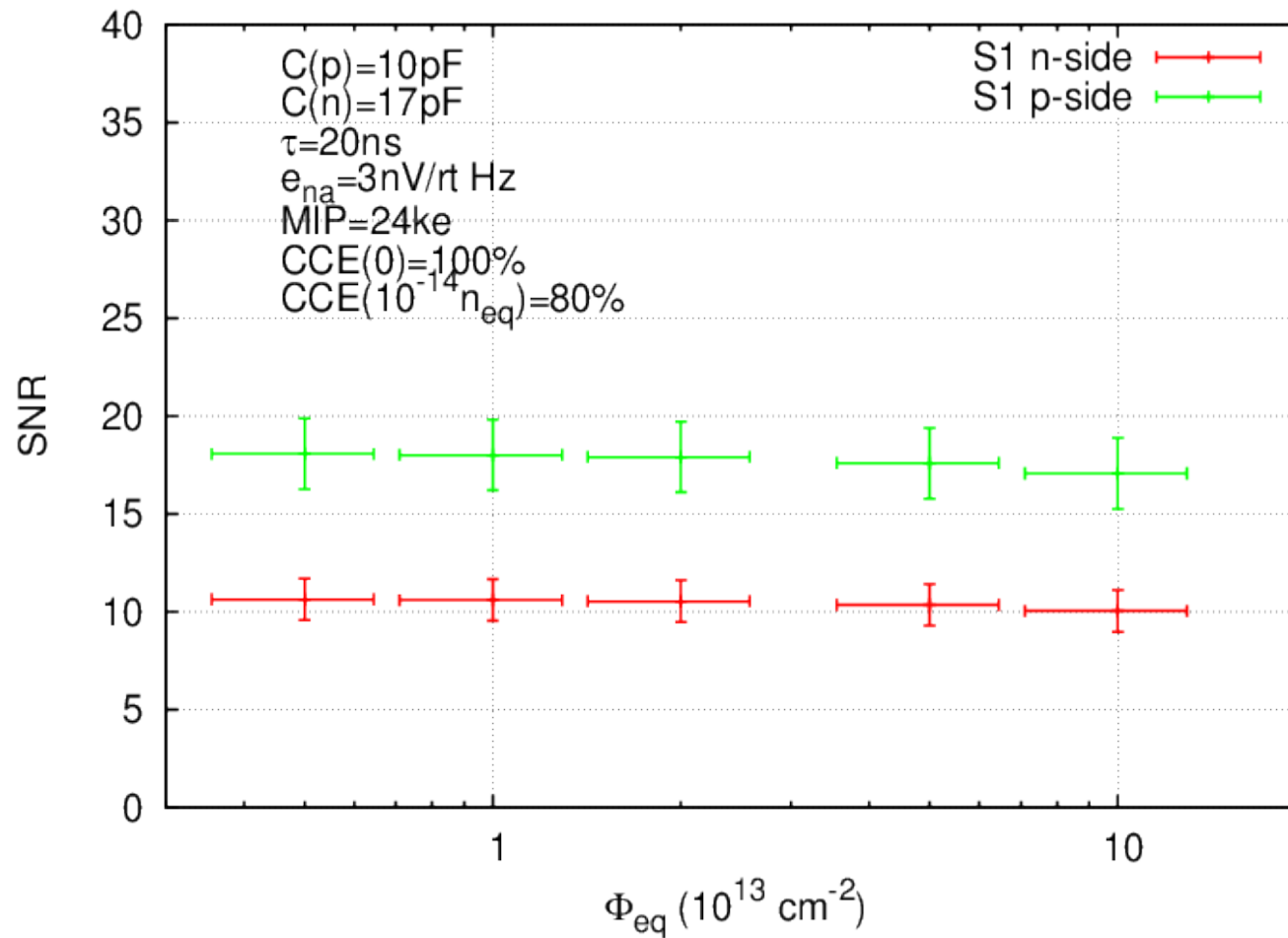
Radiation Hardness

PASTA FE ASIC:

- 20ns shaping in analog stage
- Baseline noise determines overall noise figure (ToT time jitter negligible)

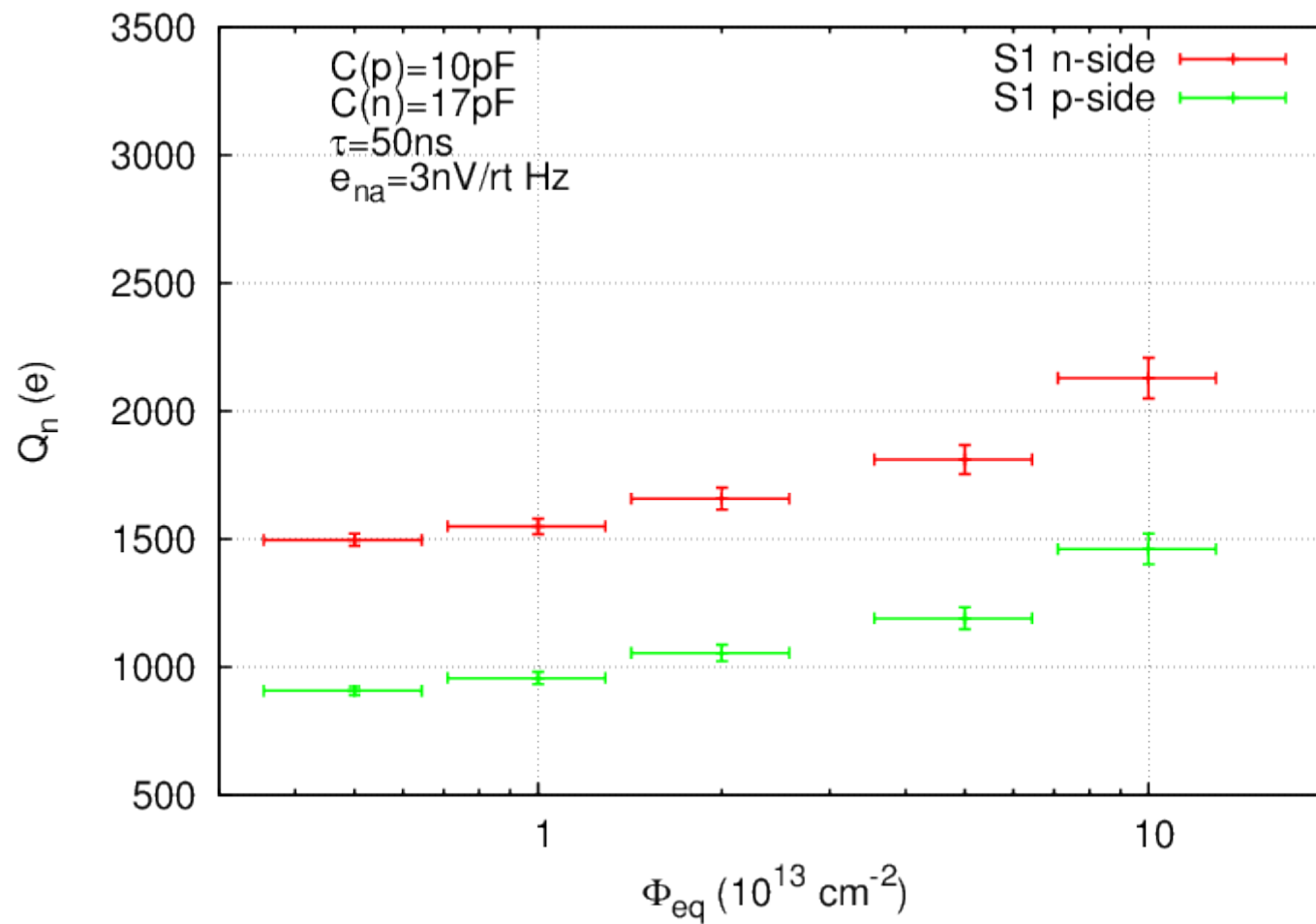


Radiation Hardness

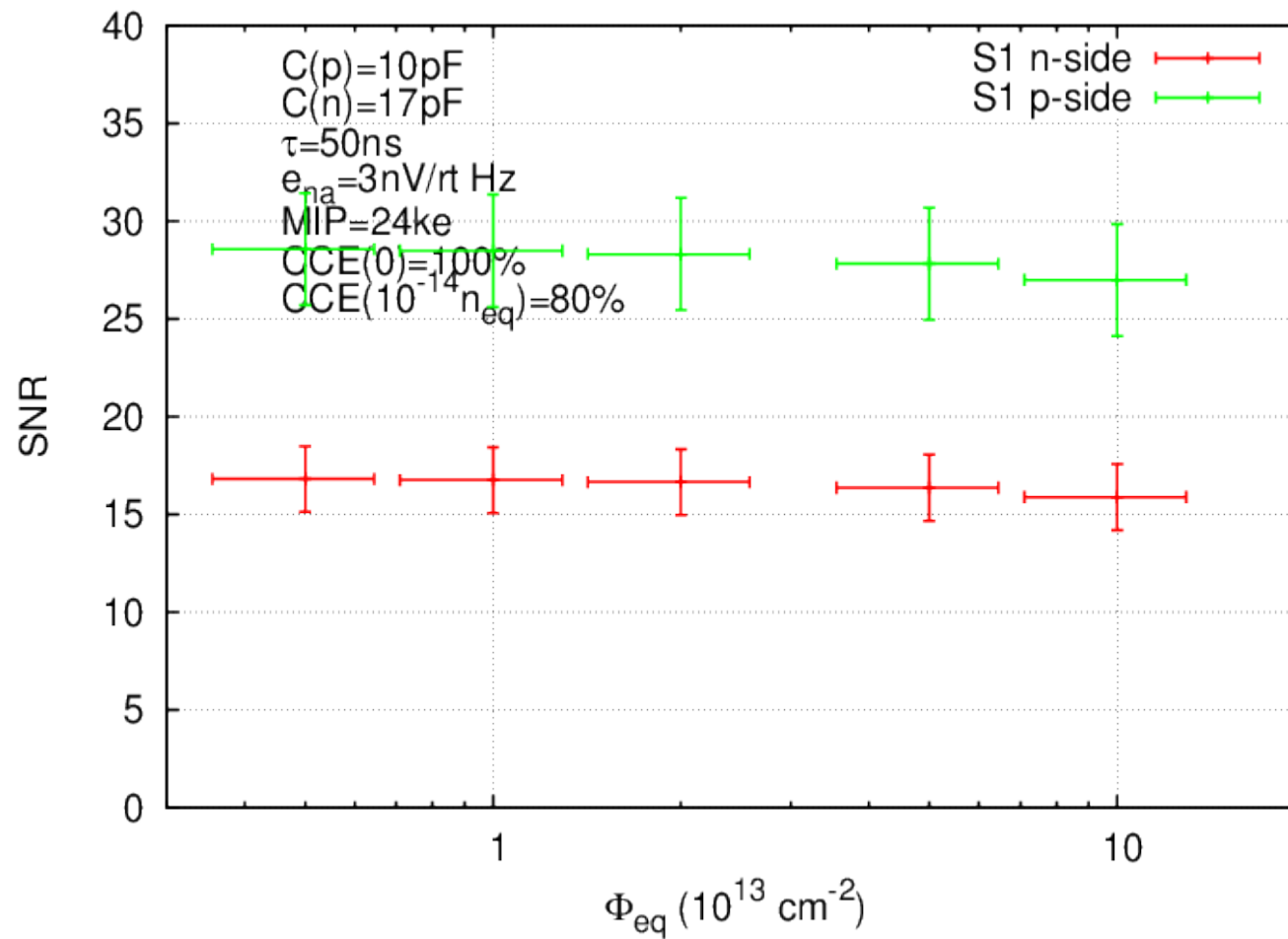


Radiation Hardness

If analog shaping time constant was 50ns



Radiation Hardness

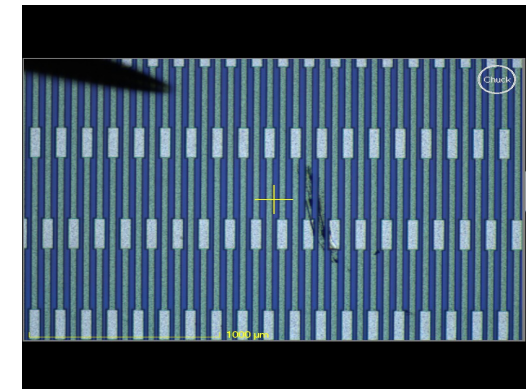
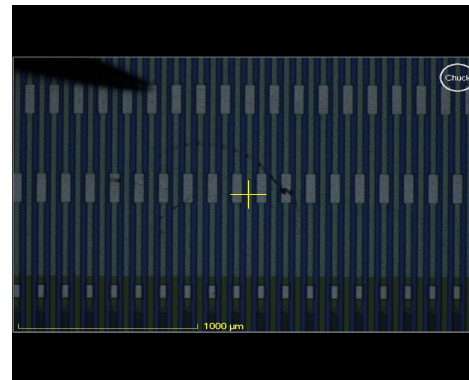
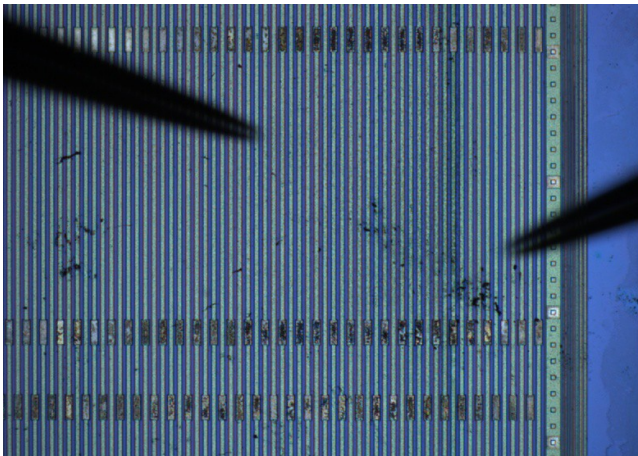


Spatial Resolution

r/o pitch (μm)	worst RMS resolution $\frac{p}{\sqrt{12}}$ (μm)	nr. of intermediate strips	SNR	spacial resolution RMS (μm)
65	18.8	0	10	16.09 ± 0.02
			16	13.08 ± 0.02
			25	10.63 ± 0.01
130	37.5	0	10	34.70 ± 0.05
			16	31.64 ± 0.04
			25	29.28 ± 0.04
130	37.5	1	10	24.92 ± 0.03
			16	16.13 ± 0.02
			25	12.11 ± 0.02
195	56.3	2	10	44.52 ± 0.06
			16	26.68 ± 0.03
			25	13.84 ± 0.02
260	75.1	3	10	54.62 ± 0.07
			16	35.92 ± 0.05
			25	18.11 ± 0.02

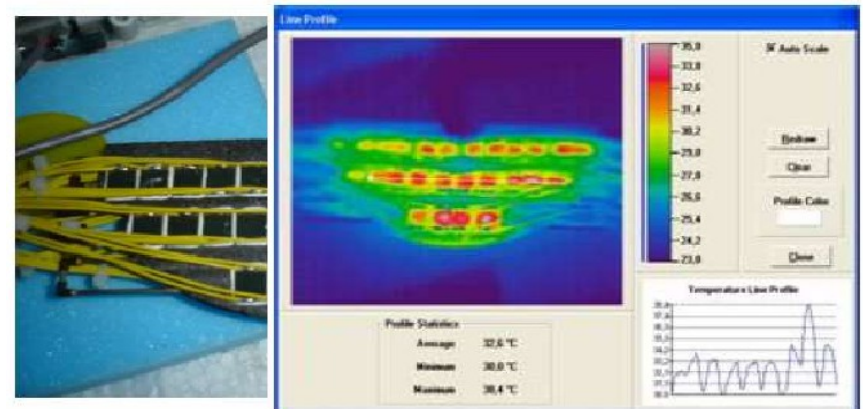
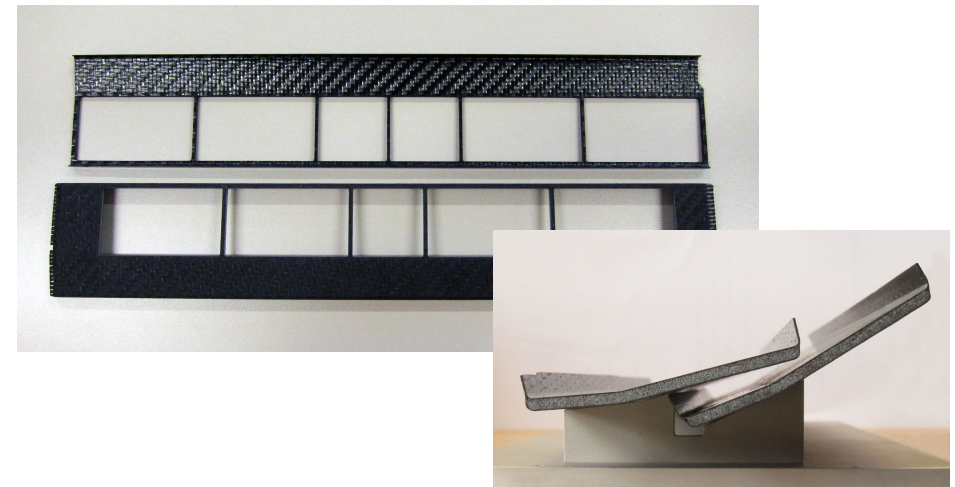
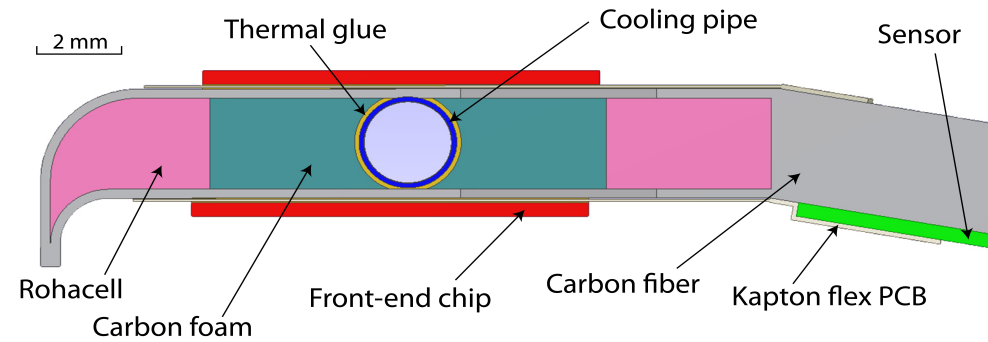
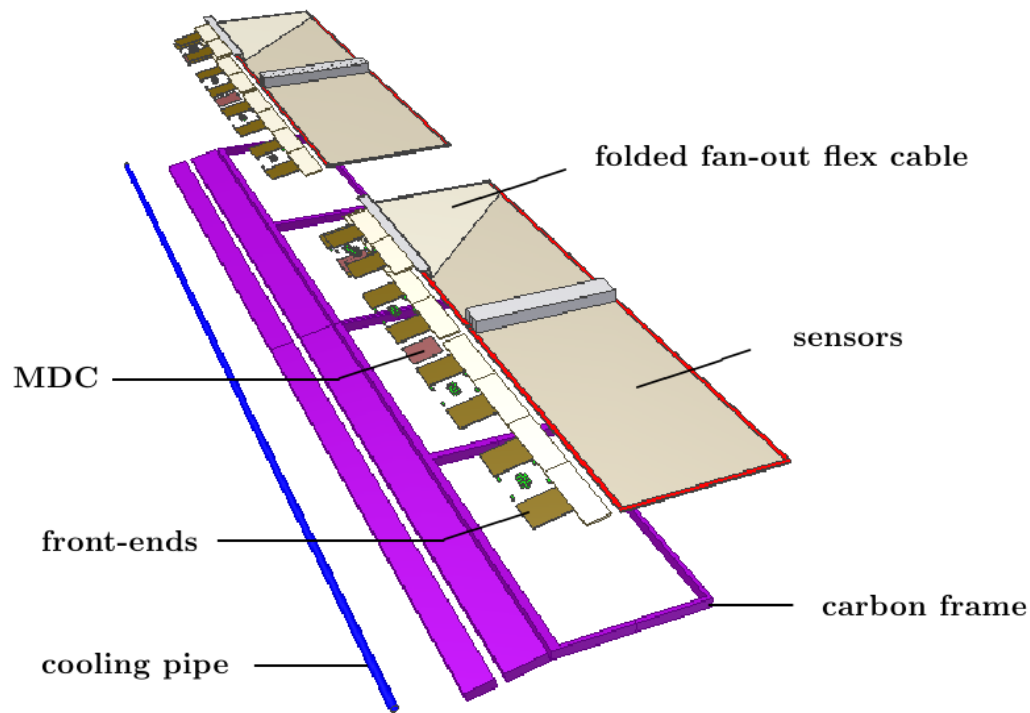
Next Steps

- Work out target specifications for sensor qualification with CIS (yield: >75% at 10 batch prod. run, on-site probing)
- Define set of additional (complementary) full sensor / wafer tests to be done in Giessen
- Set up optical inspection system with pattern recognition algorithms
- Set up QA database for sensor parameters, measurements and histories

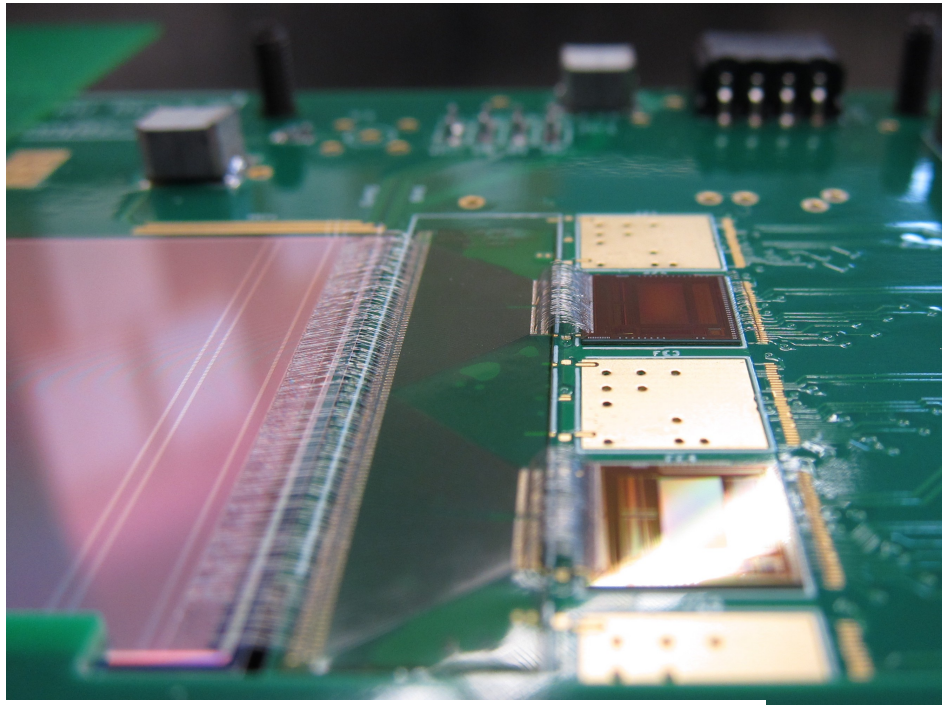


Backup Slides

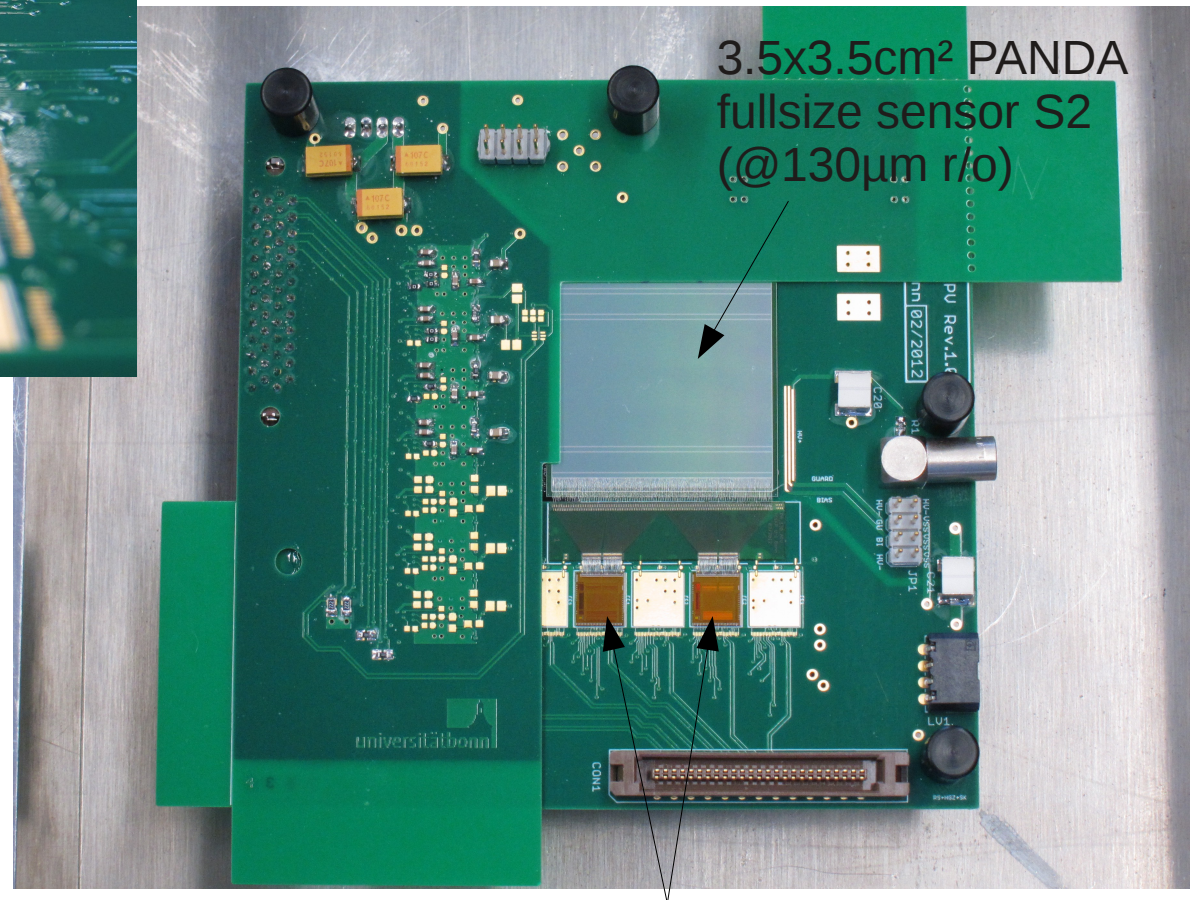
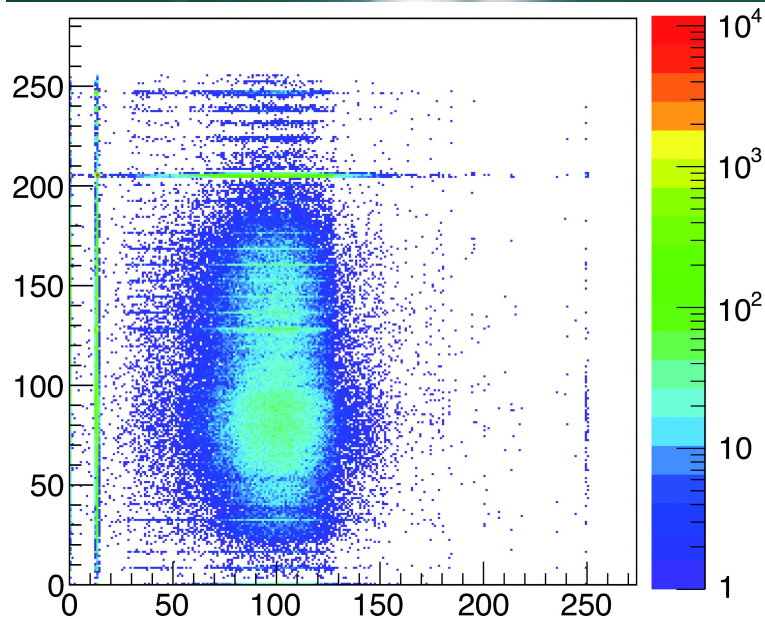
Strip Sensor Staves



Strip Sensors

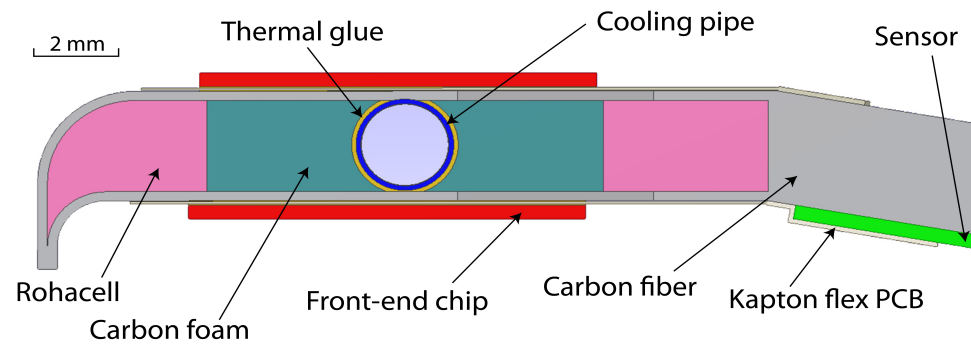
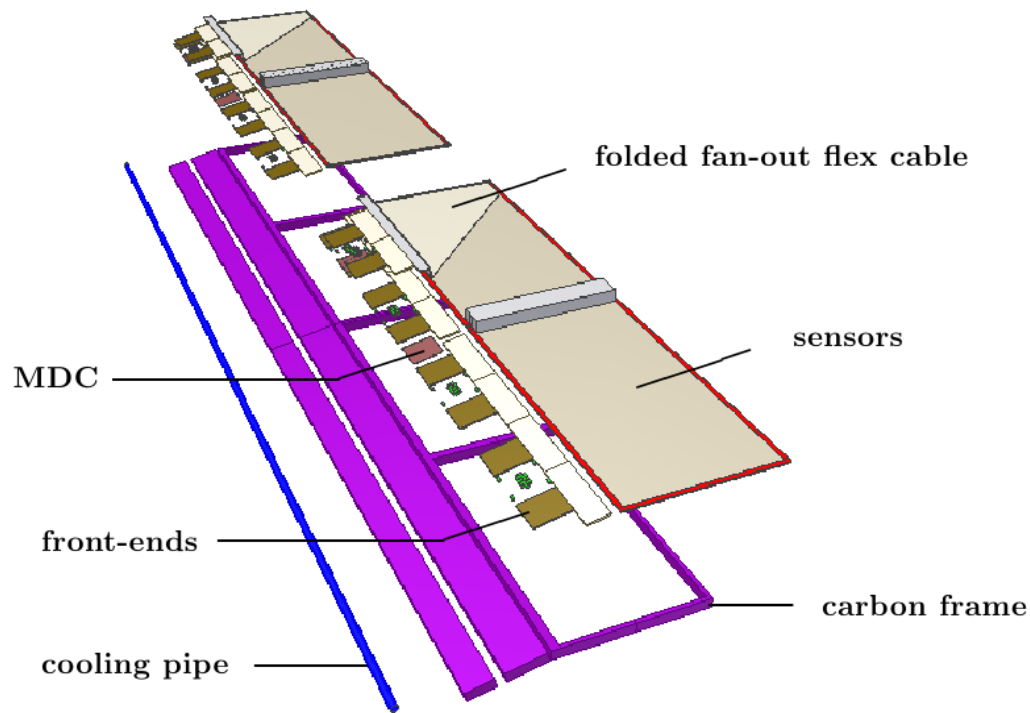


Flex-PA and squared sensor
assembled on a test board and
successfully tested at SPS, CERN
(September 2012)

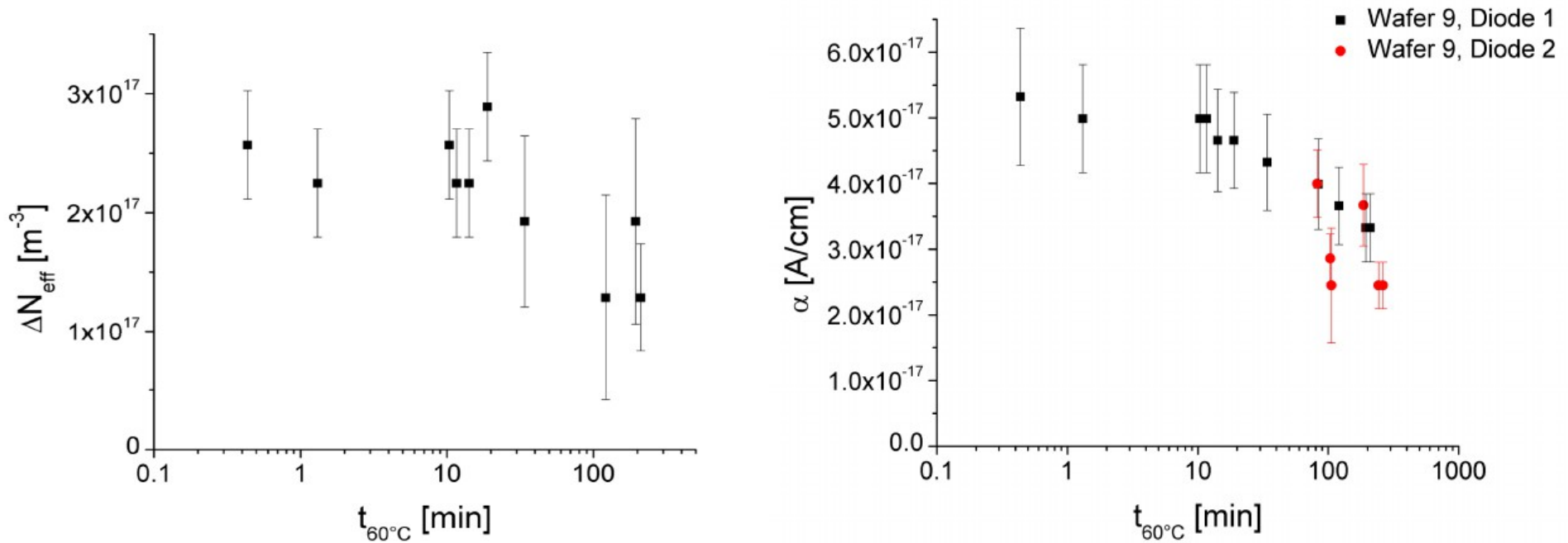


APV25 Front-ends

Grounding of Carbon Staves



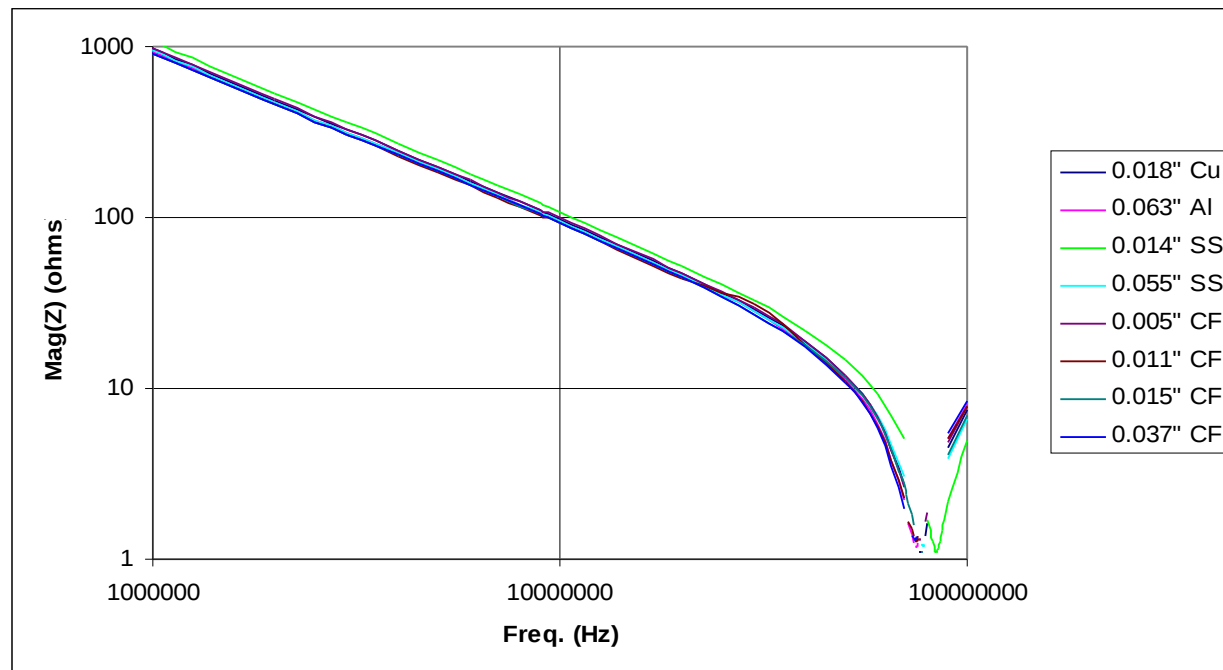
Thermal Annealing



Partial recovery of properties through thermal ordering effects = Annealing

Grounding of Carbon Staves

- Current pitch fabrication techniques that produce carbon fiber with ultra-high modulus (~ 1000 GPa) also yield very low resistivity ($\sim 100 \mu\Omega\cdot\text{cm}$)
- Floating conductors tend to strongly couple to silicon sensors
- Very nasty source of noise, esp. in densely packed structures of high impedance and highly sensitive sensors (lose coupling)



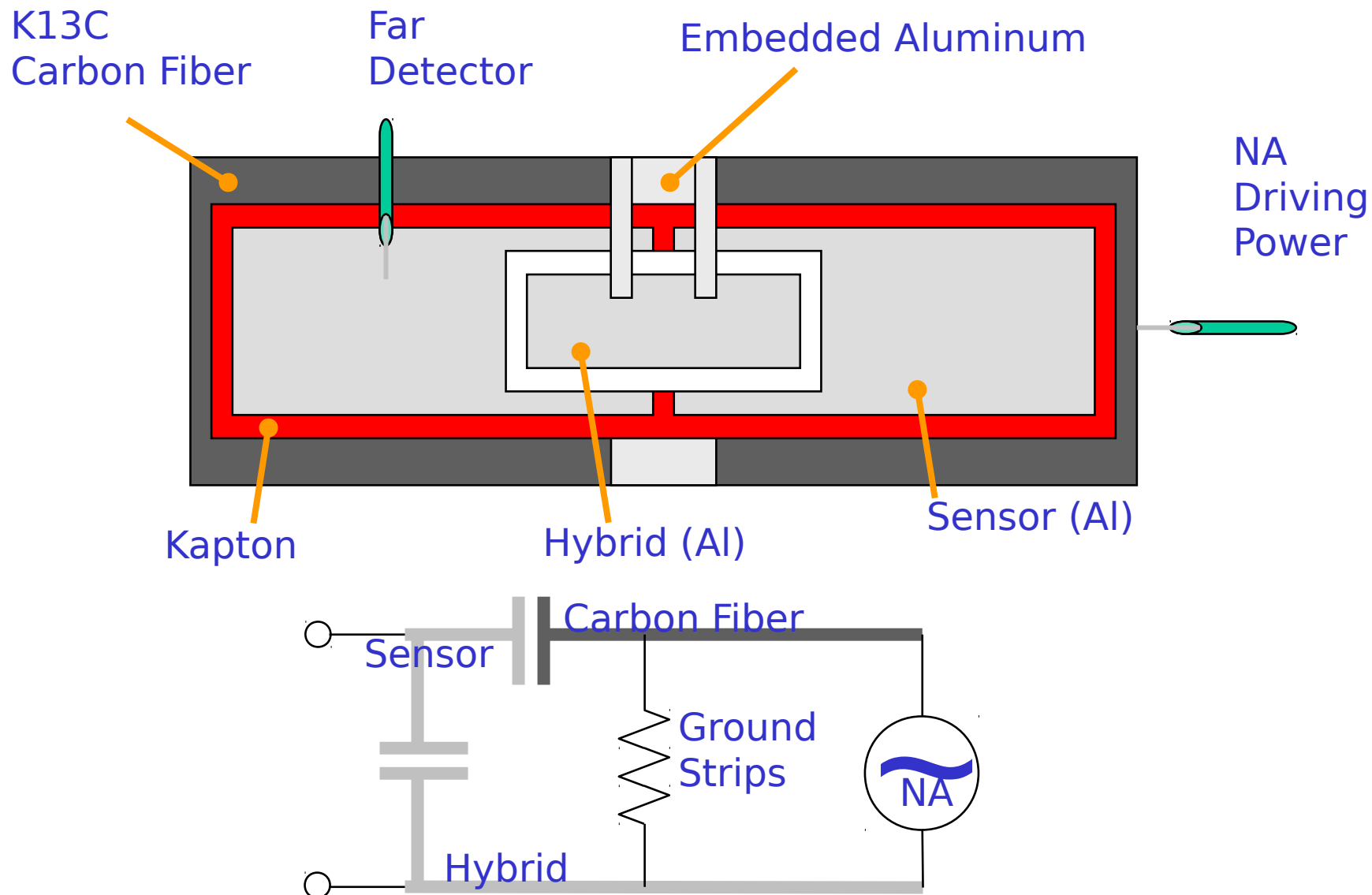
Strip Sensor Staves

D0:

- Electrical coupling of reference ground conductor to carbon stave is **crucial**
- Embed Al foils into carbon structure
- Al foil coverage of 20...25% of the carbon stave
- Oxidation and fragility of Al foil are critical

Grounding of Carbon Staves

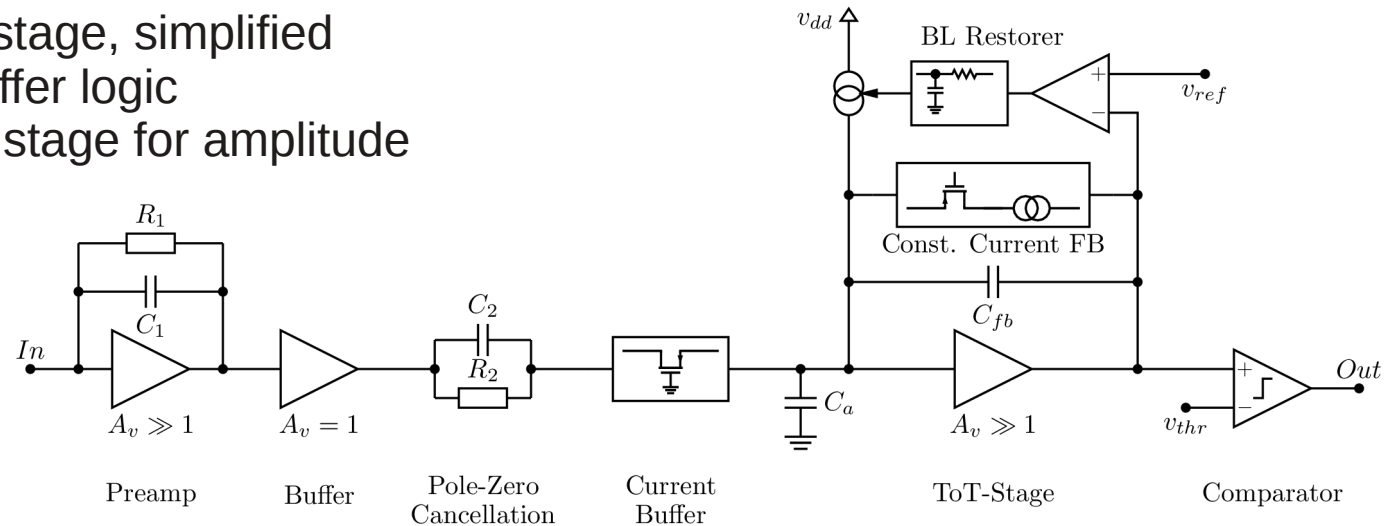
D0 L0/L1 Mock-up



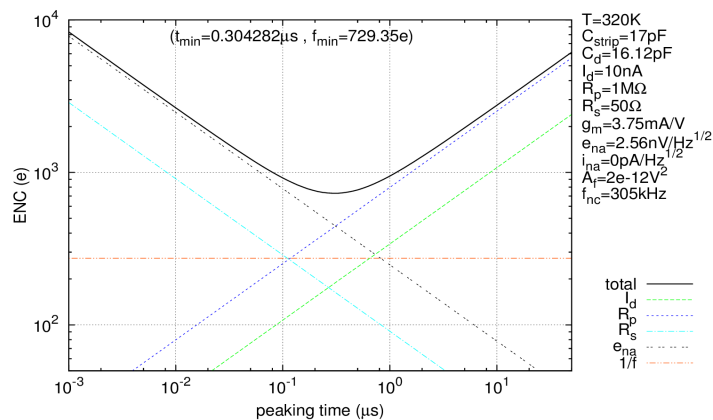
Strip Front-end

- design of new selftriggered FE based on ToPIX pixel FE started in 2012
- modified analog stage, simplified single column buffer logic
- ToT+HiRes TDC stage for amplitude measurement

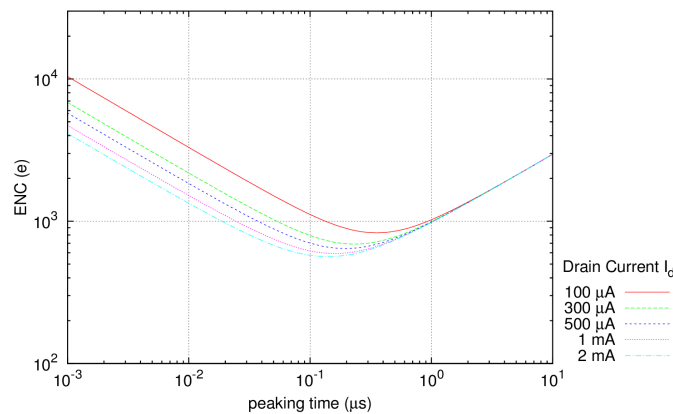
INFN Torino, JLU Giessen, IKP Jülich



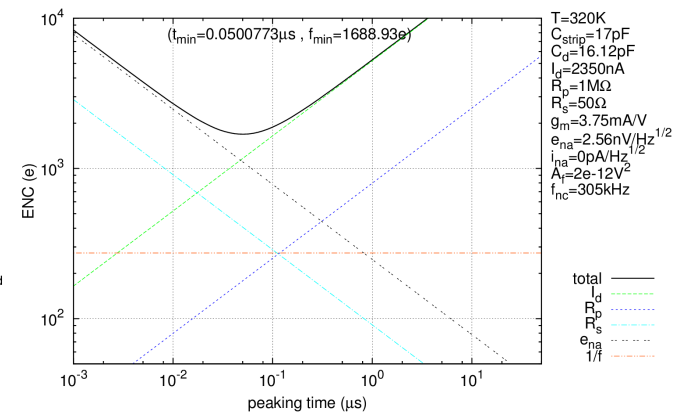
Preamp. Noise:



unirradiated



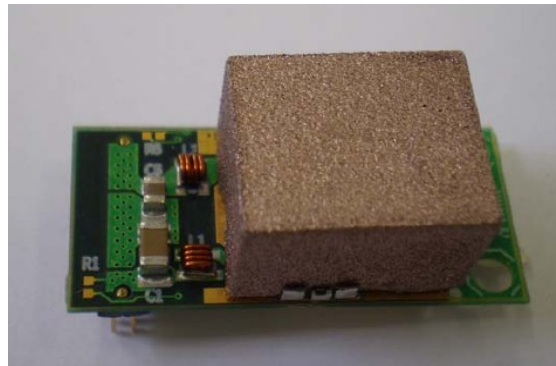
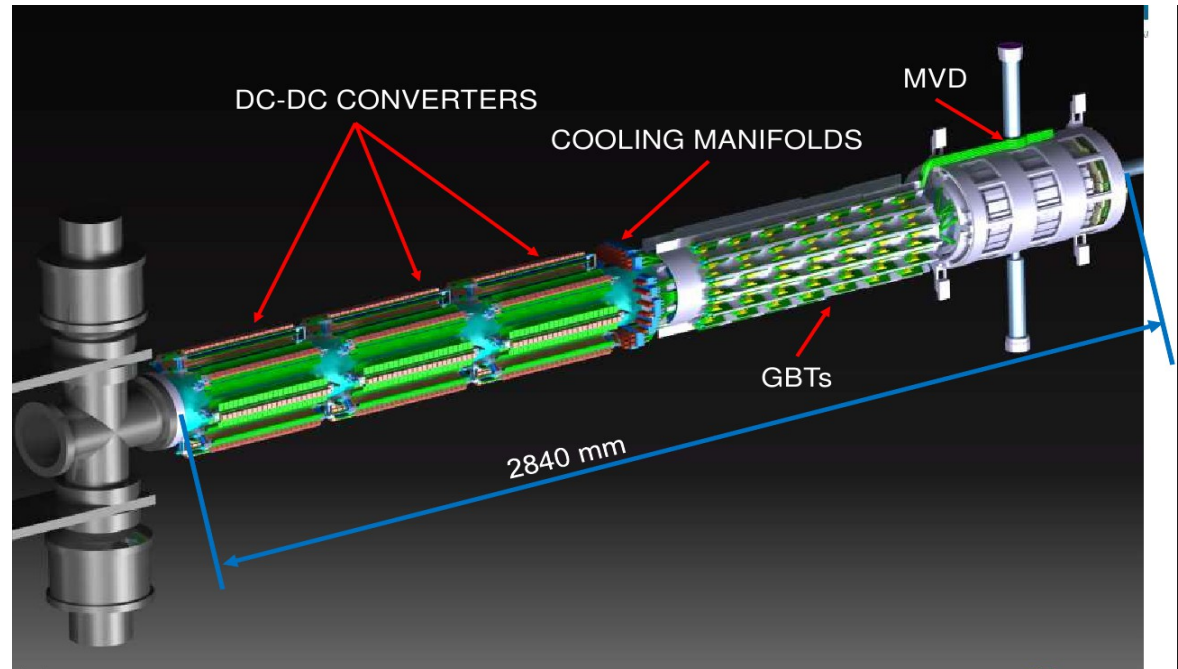
5e13 n. eq.



Powering

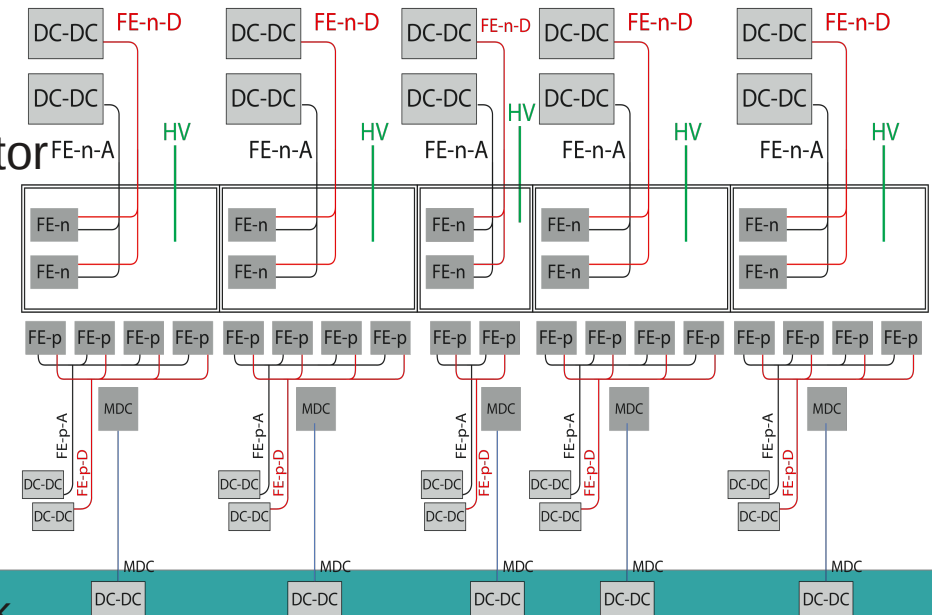
DC-DC powering concept

- Air-coil converters operate inside strong magnetic fields
- 80% efficiency
- Converter developed at CERN for LHC upgrade



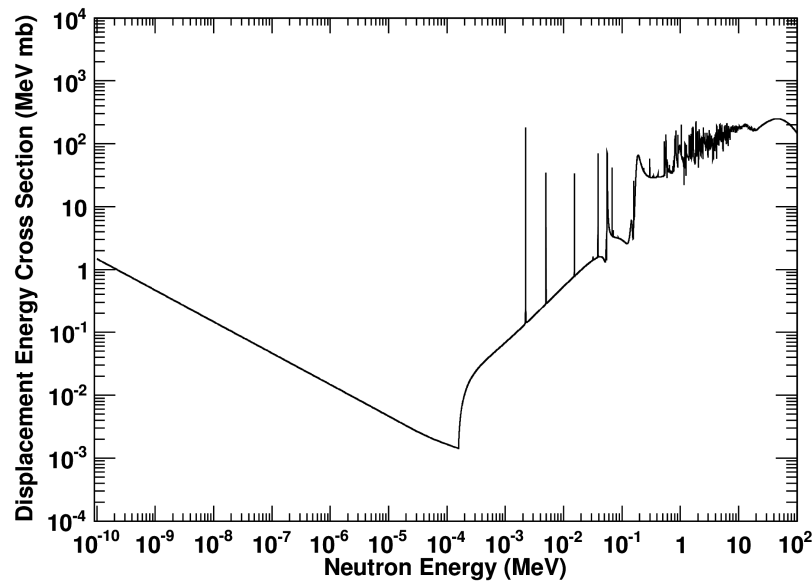
SM01C DC/DC converter

Strip subdetector powering

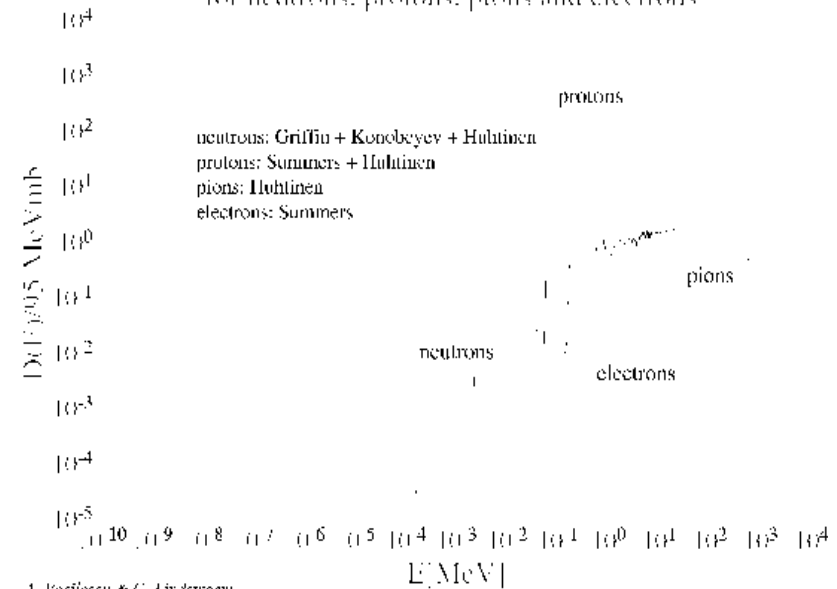


Radiation Damage

Si - compound



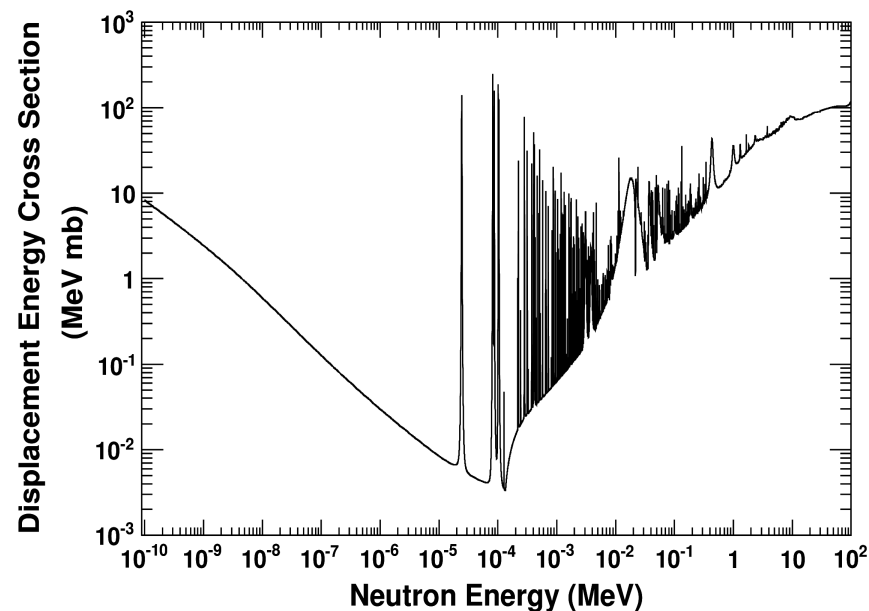
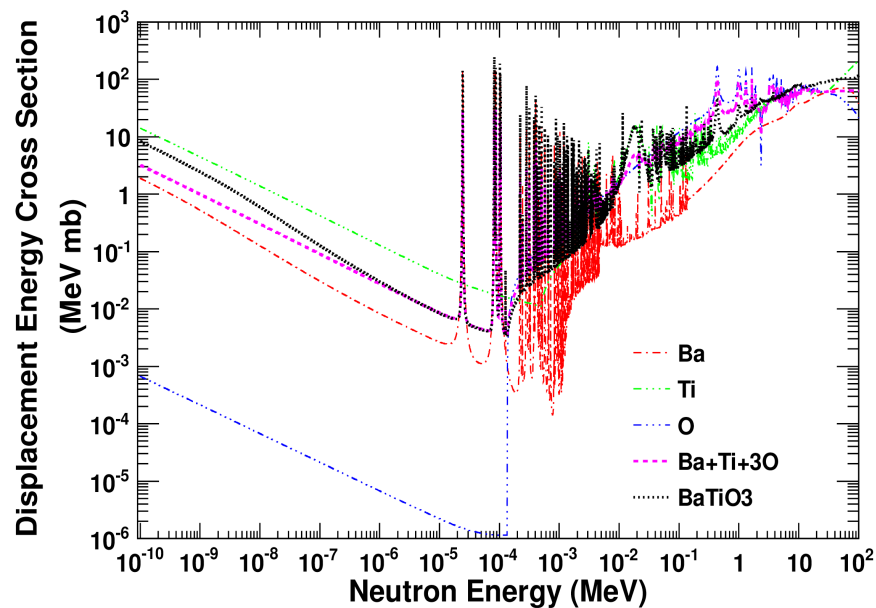
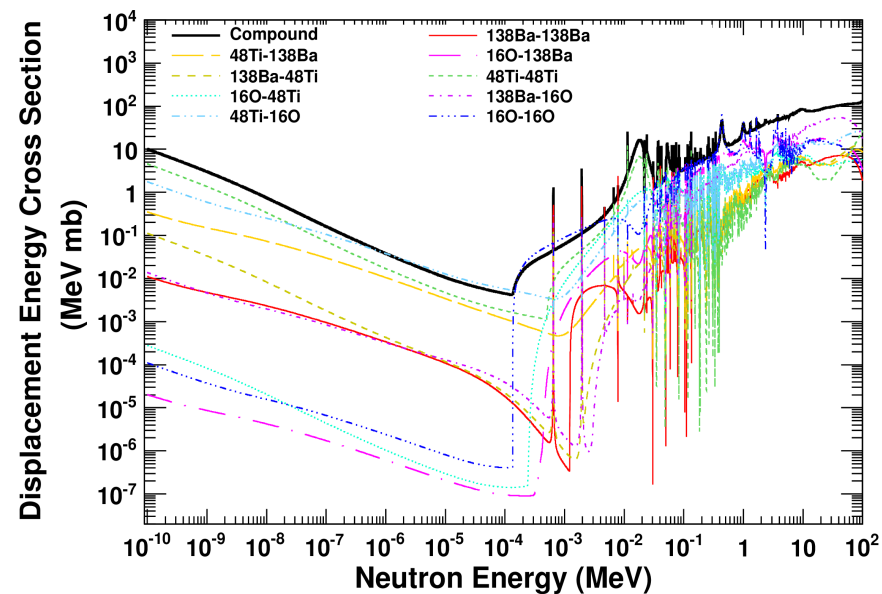
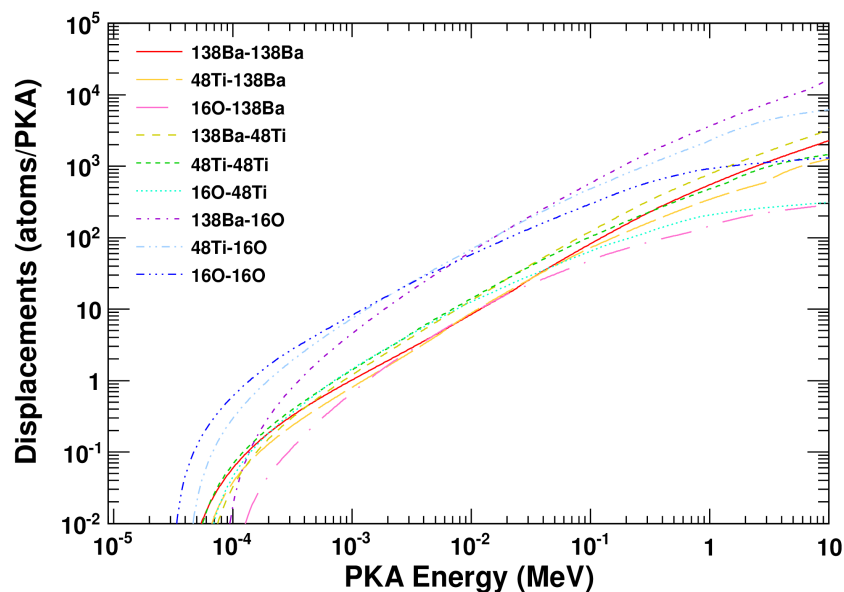
Displacement damage in Silicon
for neutrons, protons, pions and electrons



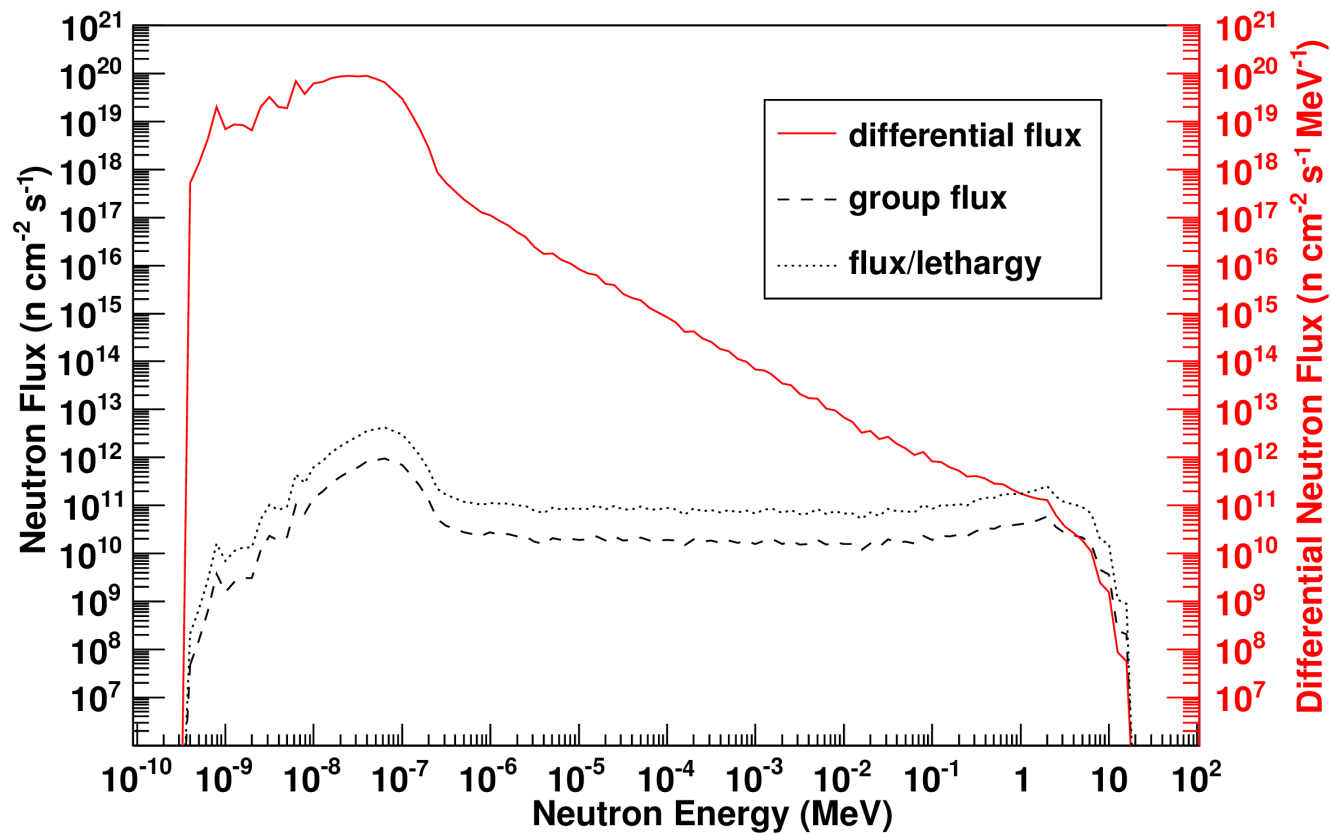
A. Vorstevan & G. Lindstrom

Radiation Damage

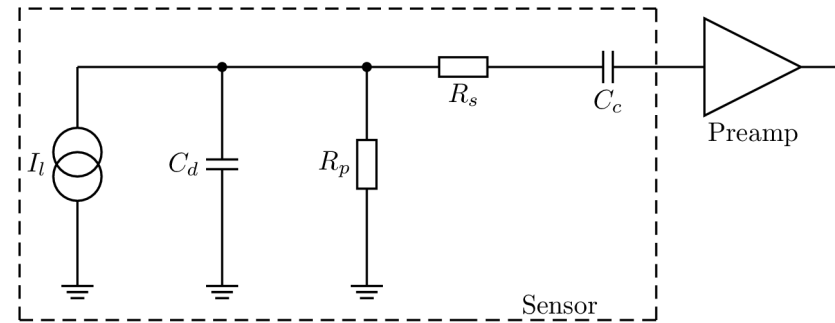
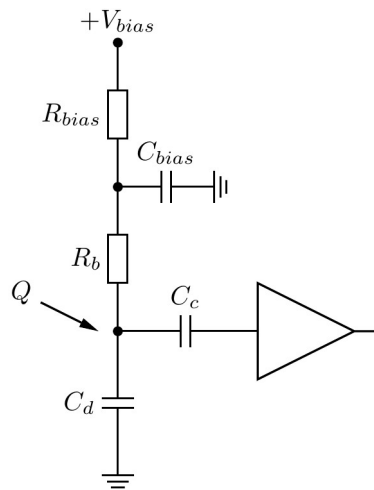
BaTiO₃ - compound



Radiation Damage



Strip Subdetector



Strip Sensors

